WeEn
WeEn Semiconductors

IMPORTANT NOTICE

10 December 2015

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors

founded by
NXP

DATA SHEET

BTA212B series B

Three quadrant triacs high commutation

Product specification

September 1997

Three quadrant triacs high commutation

BTA212B series B

GENERAL DESCRIPTION

Glass passivated high commutation triacs in a plastic envelope suitable for surface mounting intended for use in circuits where high static and dynamic dV/dt and high dI/dt can occur. These devices will commutate the full rated rms current at the maximum rated junction temperature, without the aid of a snubber.

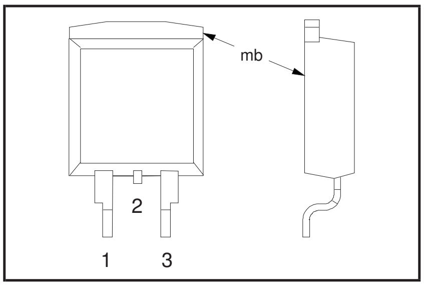
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
	BTA212B-	**500B**	**600B**	**800B**	
V_{DRM}	Repetitive peak off-state voltages	500	600	800	V
$I_{T(RMS)}$	RMS on-state current	12	12	12	A
I_{TSM}	Non-repetitive peak on-state current	95	95	95	A

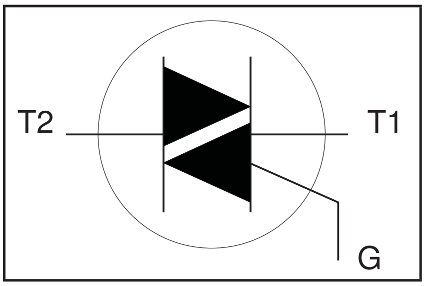
PINNING - SOT404

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
mb	main terminal 2

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
				-500	**-600**	**-800**	
V_{DRM}	Repetitive peak off-state voltages		-	500[1]	600[1]	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 99$ ˚C	-	12			A
I_{TSM}	Non-repetitive peak on-state current	full sine wave; $T_j = 25$ ˚C prior to surge					
		t = 20 ms	-	95			A
		t = 16.7 ms	-	105			A
I^2t	I^2t for fusing	t = 10 ms	-	45			A^2s
dI_T/dt	Repetitive rate of rise of on-state current after triggering	$I_{TM} = 20$ A; $I_G = 0.2$ A; $dI_G/dt = 0.2$ A/µs		100			A/µs
I_{GM}	Peak gate current		-	2			A
V_{GM}	Peak gate voltage		-	5			V
P_{GM}	Peak gate power		-	5			W
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	0.5			W
T_{stg}	Storage temperature		-40	150			˚C
T_j	Operating junction temperature		-	125			˚C

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[1] Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/µs.

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j\text{-}mb}$	Thermal resistance junction to mounting base	full cycle	-	-	1.5	K/W
		half cycle	-	-	2.0	K/W
$R_{th\ j\text{-}a}$	Thermal resistance junction to ambient	in free air	-	60	-	K/W

STATIC CHARACTERISTICS

T_j = 25 ˚C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{GT}	Gate trigger current[2]	V_D = 12 V; I_T = 0.1 A				
		T2+ G+	2	18	50	mA
		T2+ G-	2	21	50	mA
		T2- G-	2	34	50	mA
I_L	Latching current	V_D = 12 V; I_{GT} = 0.1 A				
		T2+ G+	-	31	60	mA
		T2+ G-	-	34	90	mA
		T2- G-	-	30	60	mA
I_H	Holding current	V_D = 12 V; I_{GT} = 0.1 A	-	31	60	mA
V_T	On-state voltage	I_T = 17 A	-	1.3	1.6	V
V_{GT}	Gate trigger voltage	V_D = 12 V; I_T = 0.1 A	-	0.7	1.5	V
		V_D = 400 V; I_T = 0.1 A; T_j = 125 ˚C	0.25	0.4	-	V
I_D	Off-state leakage current	V_D = $V_{DRM(max)}$; T_j = 125 ˚C	-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

T_j = 25 ˚C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV_D/dt	Critical rate of rise of off-state voltage	V_{DM} = 67% $V_{DRM(max)}$; T_j = 125 ˚C; exponential waveform; gate open circuit	1000	4000	-	V/µs
dI_{com}/dt	Critical rate of change of commutating current	V_{DM} = 400 V; T_j = 125 ˚C; $I_{T(RMS)}$ = 12 A; without snubber; gate open circuit	-	24	-	A/ms
t_{gt}	Gate controlled turn-on time	I_{TM} = 12 A; V_D = $V_{DRM(max)}$; I_G = 0.1 A; dI_G/dt = 5 A/µs	-	2	-	µs

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[2] Device does not trigger in the T2-, G+ quadrant.

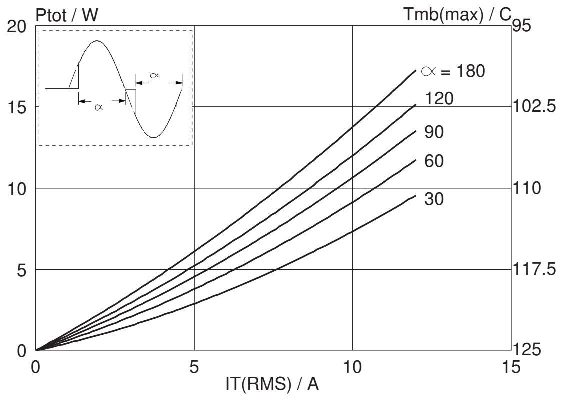

Fig.1. Maximum on-state dissipation, P_{tot}, versus rms on-state current, $I_{T(RMS)}$, where α = conduction angle.

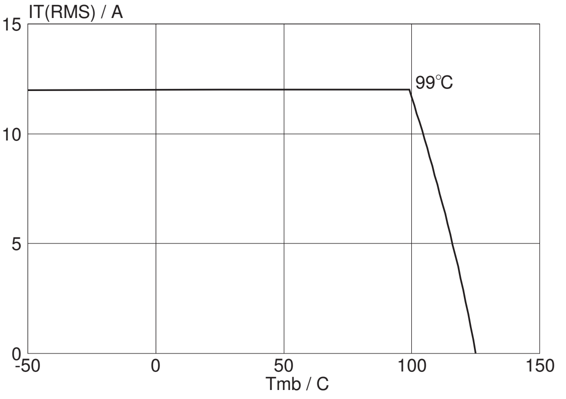

Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus mounting base temperature T_{mb}.

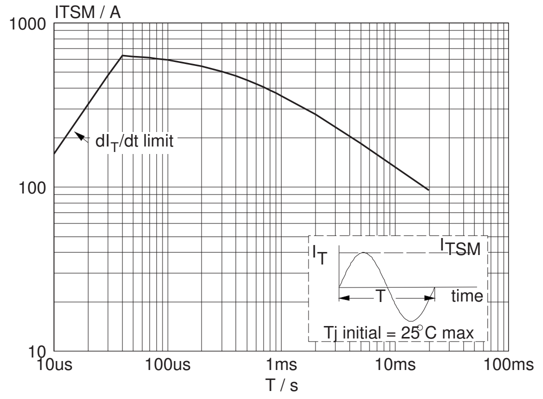

Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM}, versus pulse width t_p, for sinusoidal currents, $t_p \leq 20$ms.

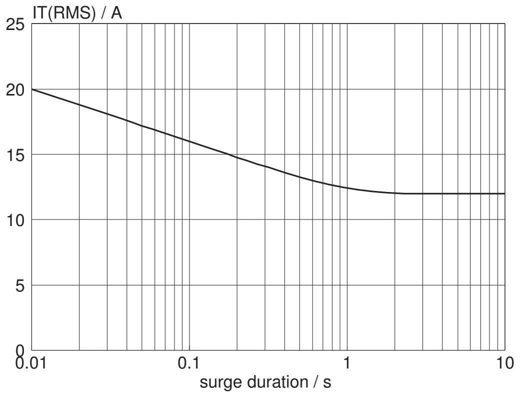

Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{mb} \leq 99$˚C.

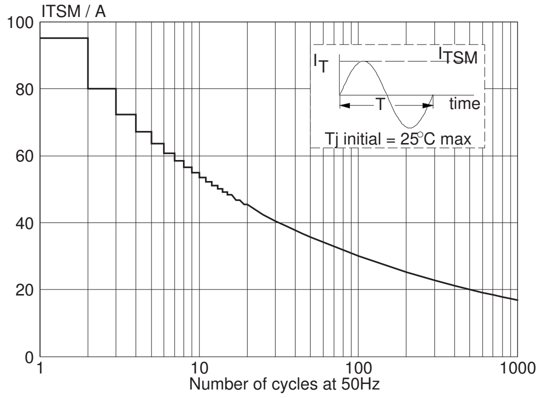

Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM}, versus number of cycles, for sinusoidal currents, f = 50 Hz.

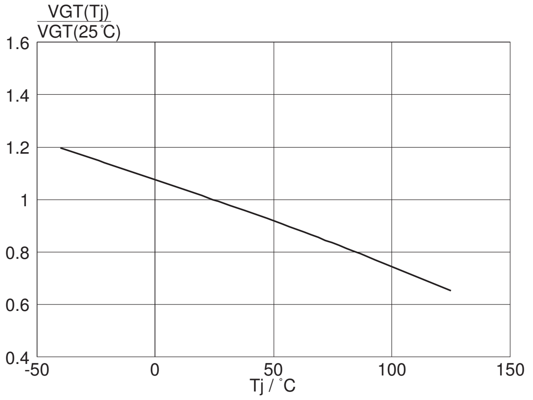

Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)/ V_{GT}(25˚C)$, versus junction temperature T_j.

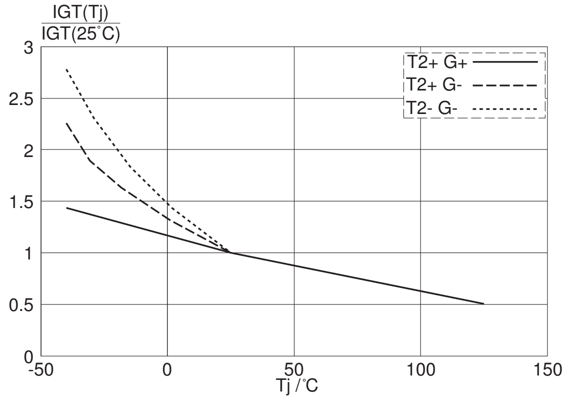

Fig.7. Normalised gate trigger current $I_{GT}(T_j)/\ I_{GT}(25˚C)$, versus junction temperature T_j.

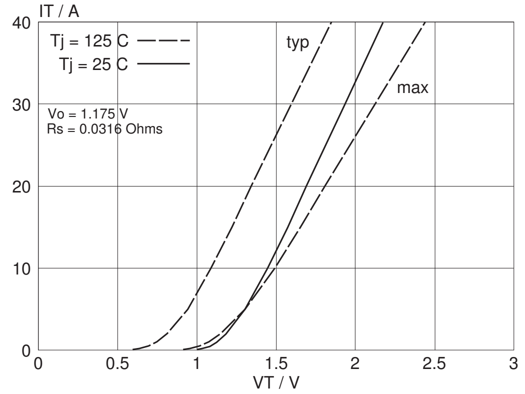

Fig.10. Typical and maximum on-state characteristic.

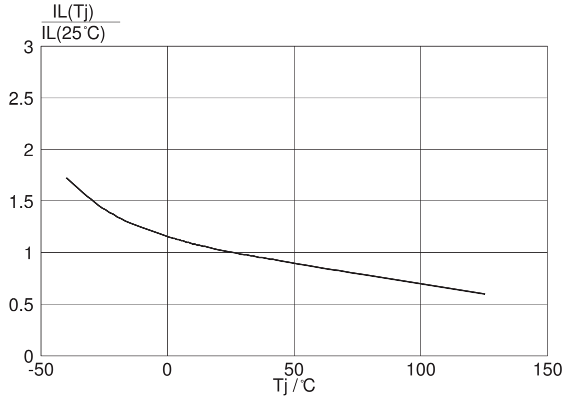

Fig.8. Normalised latching current $I_L(T_j)/\ I_L(25˚C)$, versus junction temperature T_j.

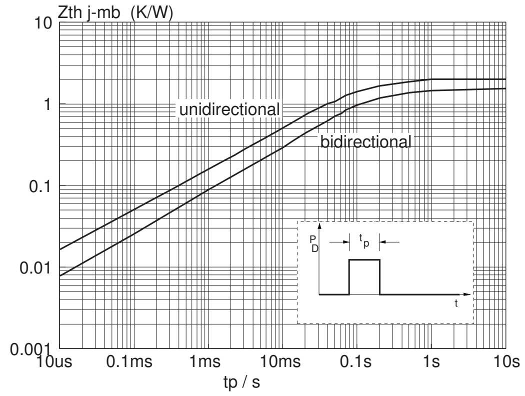

Fig.11. Transient thermal impedance $Z_{th\ j\text{-}mb}$, versus pulse width t_p.

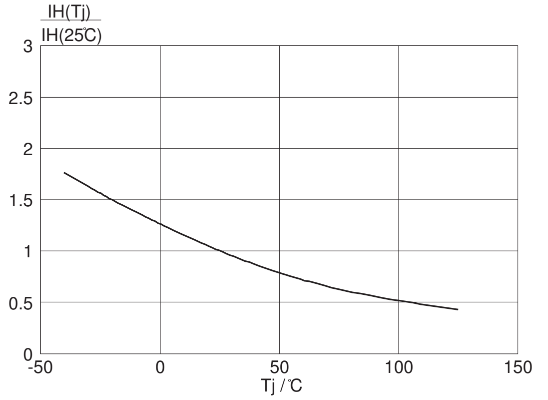

Fig.9. Normalised holding current $I_H(T_j)/\ I_H(25˚C)$, versus junction temperature T_j.

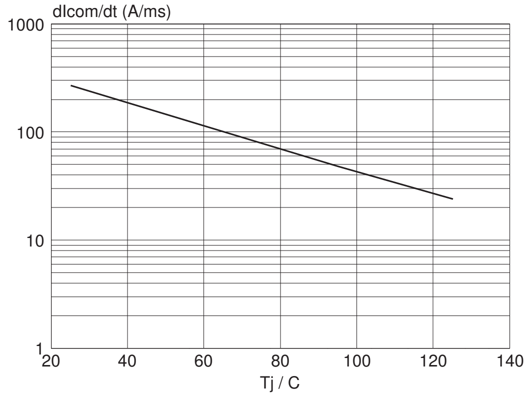

Fig.12. Typical, critical rate of change of commutating current dI_{com}/dt versus junction temperature.

MECHANICAL DATA

Dimensions in mm

Net Mass: 1.4 g

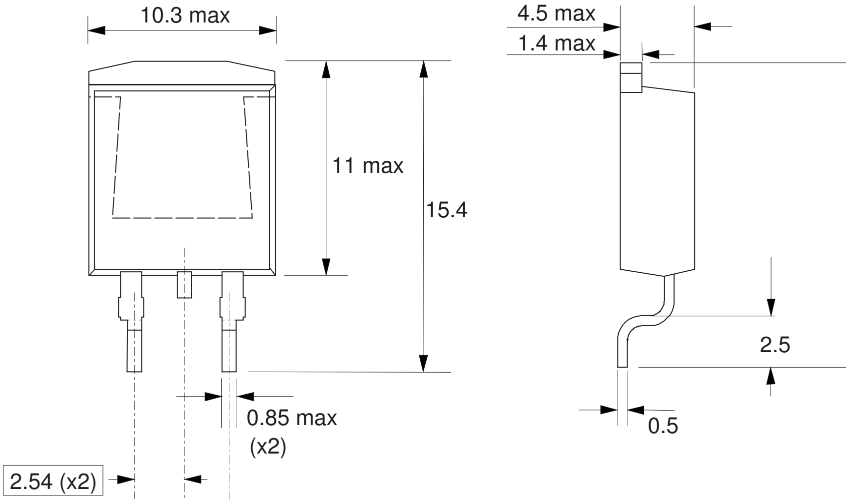

Fig.13. SOT404 : centre pin connected to mounting base.

Notes
1. Epoxy meets UL94 V0 at 1/8".

MOUNTING INSTRUCTIONS

Dimensions in mm

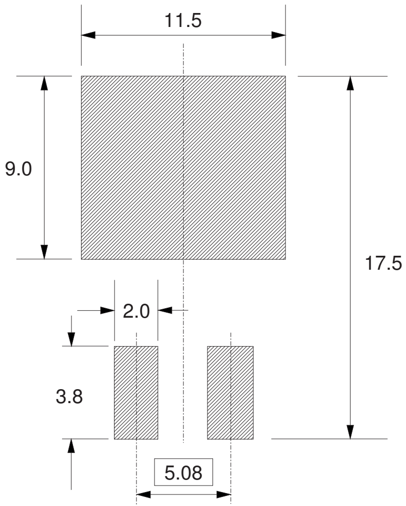

Fig.14. SOT404 : minimum pad sizes for surface mounting.

Notes
1. Plastic meets UL94 V0 at 1/8".

Legal information

DATA SHEET STATUS

DOCUMENT STATUS(1)	PRODUCT STATUS(2)	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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